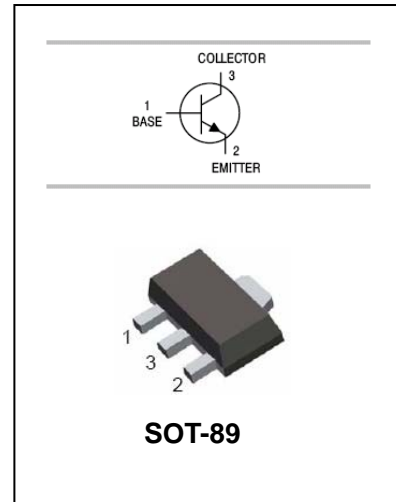


SILICON PNP EPITAXIAL TYPE TRANSISTOR

HM879

FEATURES

- Charger-up time is about 1 mS faster Than of a germanium transistor.
- Small saturation voltage can bring dissipation And flasing times.



ORDERING INFORMATION

Type No.	Marking	Package Code
HM879	879	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	30	V
V _{CEX}	Collector-Emitter Voltage	20	V
V _{CEO}	Collector-Emitter Voltage	10	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current –Continuous –Pluse	3 5	A
P _C	Collector Dissipation	1	W
T _j , T _{stg}	Junction and Storage Temperature	-55~150	°C

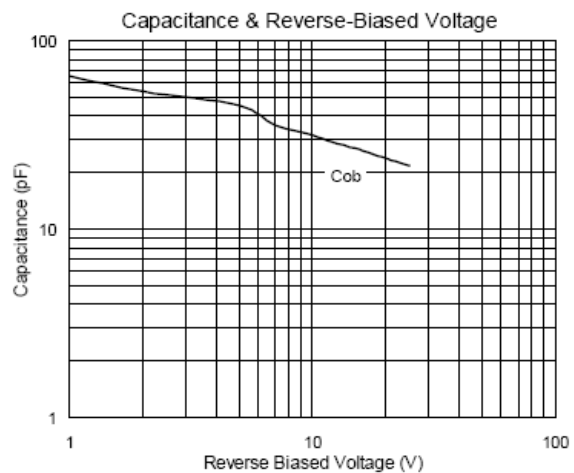
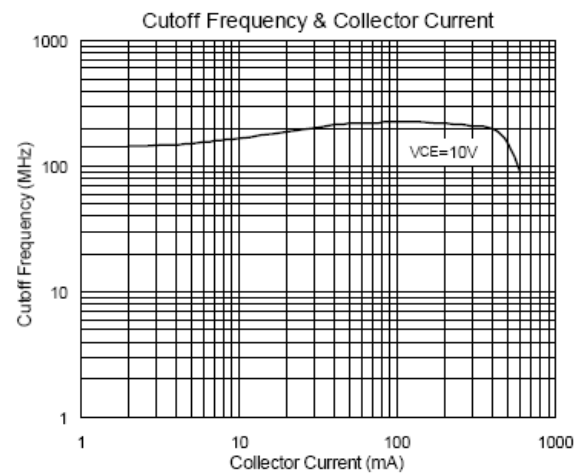
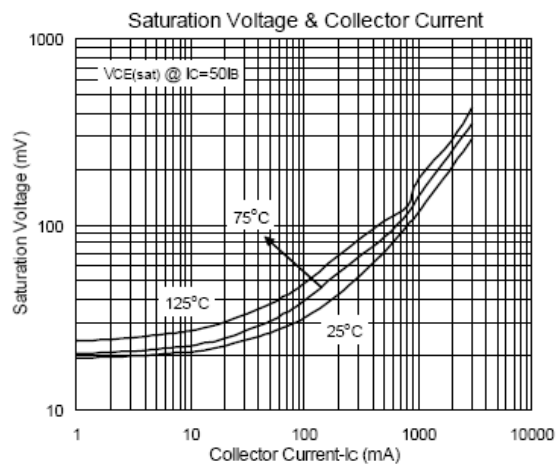
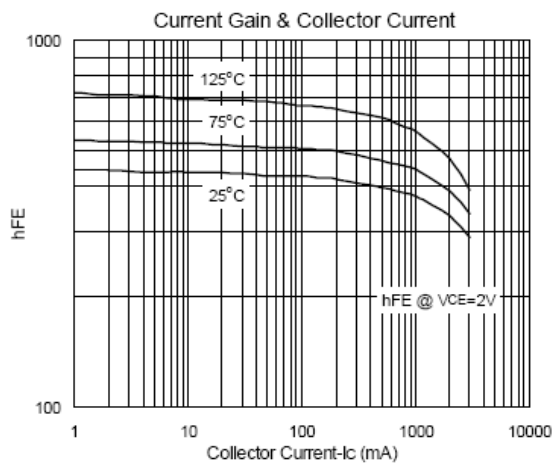
SILICON PNP EPITAXIAL TYPE TRANSISTOR

HM879

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	10			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector to Emitter Voltage	$V_{(BR)CEX}$	$I_C=1mA, V_{BE}=3V$	20			V
Collector cut-off current	I_{CBO}	$V_{CB}=20V, I_E=0$			100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0$			100	nA
DC current gain	h_{FE}	$V_{CE}=2V, I_C=3A$	140	210	400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3A, I_B=60mA$		0.3	0.4	V
Transition frequency	f_T	$V_{CE}=10V, I_C=50mA$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		30		pF

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



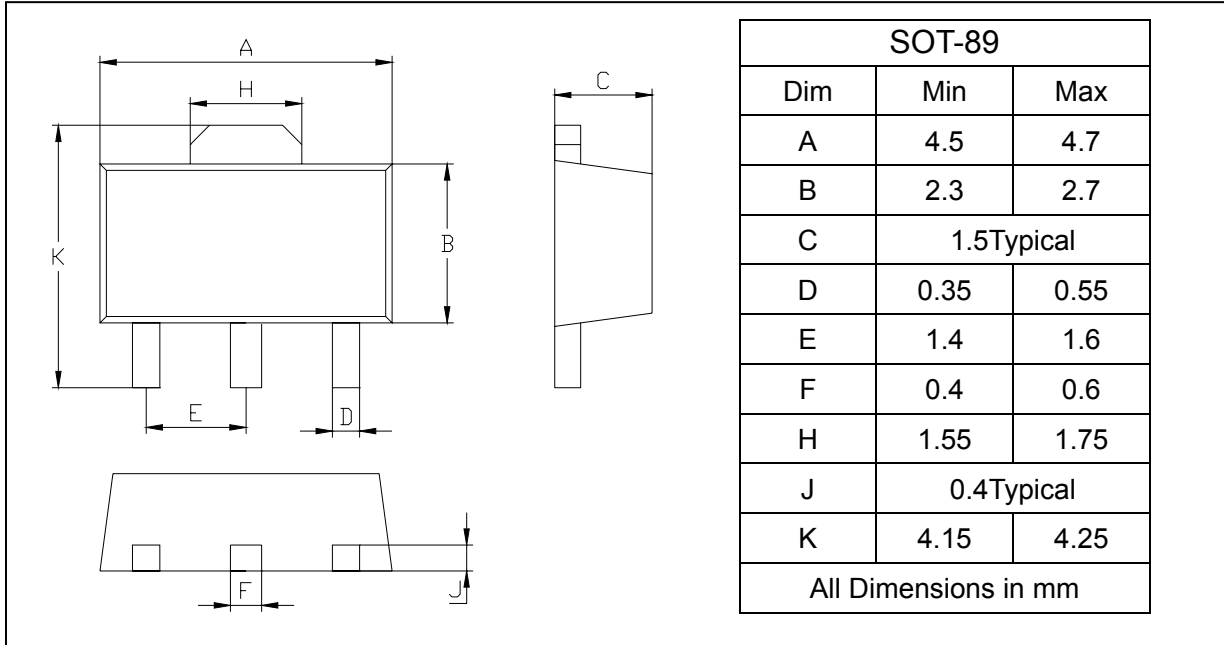
SILICON PNP EPITAXIAL TYPE TRANSISTOR

HM879

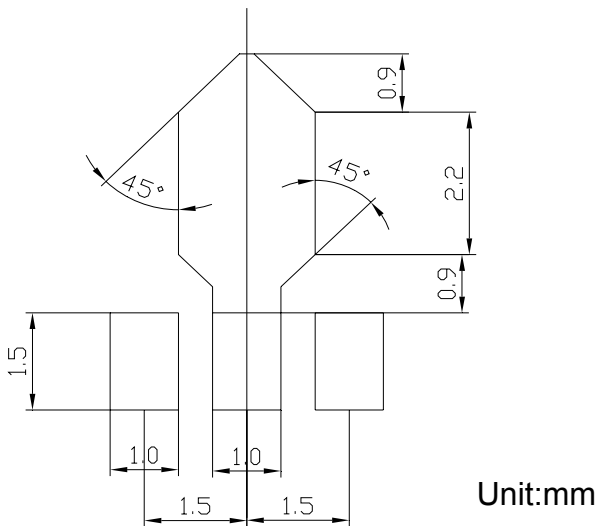
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
HM879	SOT-89	1000/Tape&Reel

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